(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
28 February 2013 (28.02.2013)

WIPO | PCT

(10) International Publication Number
WO 2013/026175 A1

(51) International Patent Classification:
H01L 27/146 (2006.01)

(21) International Application Number:
PCT/CH2012/000201

(22) International Filing Date:
24 August 2012 (24.08.2012)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
61/527,355 25 August 2011 (25.08.2011) US

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(81) Designated States *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BN, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PE, PG, PH, PL, PT, QA, RO, RS, RU, RW, SC, SD, SE, SG, SK, SL, SM, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(84) Designated States *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, GH, GM, KE, LR, LS, MW, MZ, NA, RW, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, RU, TJ, TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

— *with international search report (Art. 21(3))*

— *before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments (Rule 48.2(h))*

(54) **Title**: WAFER-LEVEL FABRICATION OF OPTICAL DEVICES WITH FRONT FOCAL LENGTH CORRECTION

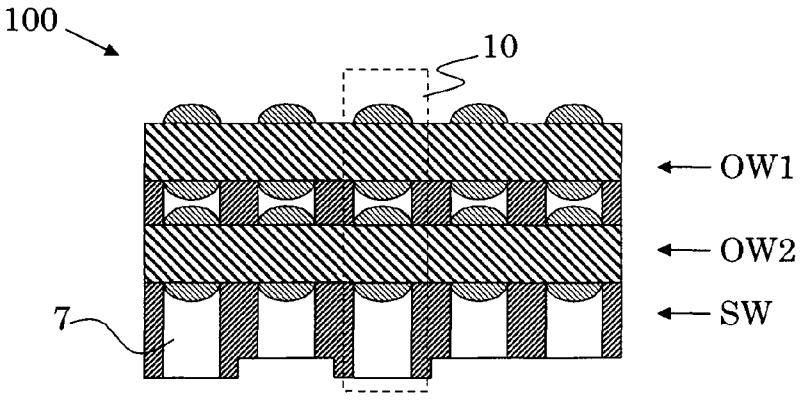


Fig. 4

(57) **Abstract**: The wafer stack (100) comprises a first wafer (OW1) referred to as optics wafer and a second wafer (SW) referred to as spacer wafer, said optics wafer (OW1) having manufacturing irregularities. The spacer wafer (SW) is structured such that it at least partially compensates for said manufacturing irregularities. The corresponding method for manufacturing a device, which in particular can be an optical device, comprises carrying out a correction step for at least partially compensating for manufacturing irregularities. Such a correction step comprises providing a wafer (SW) referred to as spacer wafer, wherein that spacer wafer is structured for at least partially compensating for said manufacturing irregularities. Those manufacturing irregularities may comprise a deviation from a nominal value, e.g., a irregularities in focal length. The invention can allow to mass produce high-precision devices at a high yield.

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